

ABSTRACT OF THE DISCLOSURE

The invention relates to a halftone phase shift photomask which is controlled with precision in terms of its transmittance at a wavelength applied to inspection, and measuring equipment, so that its quality can easily be assured even when its phase difference at an exposure wavelength is controlled at  $180^\circ\text{C}$  with precision and its transmittance is set at 1 to 20% as desired at that wavelength. The halftone phase shift photomask (107)

comprises on a transparent substrate (101) and a halftone phase shift film containing at least tantalum, oxygen, carbon and nitrogen, and has a multilayer structure comprising at least two or more different layers (102) and (103).

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